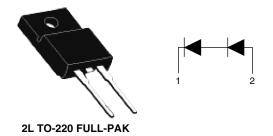


Vishay High Power Products

Hyperfast Rectifier, 8 A



PRODUCT SUMMARY				
t _{rr}	19 ns			
I _{F(AV)}	8 A			
V _R	600 V			

FEATURES

- Hyperfast recovery time
- · Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature
- Designed and qualified for industrial level



DESCRIPTION

8S2TH06FP 600 V series are the state of the art tandem hyperfast recovery rectifiers: excellent switching performance and extremely low forward voltage drop trade off is overcome, boosting overall application performance. Specially designed for CCM PFC application, these devices

show incomparable performance in every current intensive hard switching application.

Optimized reverse recovery stored charge enables downsizing of boosting switch and cooling system, increased operating frequency make possible use of smaller reactive elements. Cost effective PFC application is then possible with high efficiency over wide input voltage range and loading factor.

Plastic insulated package features easy mounting together with not insulated parts.

ABSOLUTE MAXIMUM RATINGS FOR BOTH DIODES					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Repetitive peak reverse voltage	V_{RRM}		600	V	
DC forward current	I _F	50 % duty cycle, rect. waveforms, T _C = 93 °C	8	Α	
Non-repetitive peak surge current	I _{FSM}	T _C = 25 °C	100		
Operating junction and storage temperatures	T _J , T _{Stg}		- 55 to 175	°C	

ELECTRICAL SPECIFICATIONS FOR BOTH DIODES (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _r	I _R = 100 μA	600	-	-	
Forward voltage V _F	I _F = 8 A	-	2.1	2.4	V	
	V_{F}	I _F = 8 A, T _J = 125 °C	-	1.7	2	
	I _F = 8 A, T _J = 150 °C	-	1.6	1.8		
		V _R = V _R rated	-	< 1	10	
Reverse leakage current	I_R	T _J = 125 °C, V _R = V _R rated	-	7	80	μΑ
		T _J = 150 °C, V _R = V _R rated	-	27	100	
Junction capacitance	C _T	V _R = 600 V	-	12	-	pF

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New Product

8S2TH06FP

Vishay High Power Products Hyperfast Rectifier, 8 A



DYNAMIC RECOVERY CHARACTERISTICS FOR BOTH DIODES (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, dI_F/dt = -50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	-	25		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	19	-	ns	
		T _J = 125 °C		-	35	-		
Peak recovery current I _{RRM}	I _{RRM}	T _J = 25 °C	$I_F = 8 \text{ A}$ $dI_F/dt = -200 \text{ A/}\mu\text{s}$ $V_B = 390 \text{ V}$	-	2.8	-	^	
		T _J = 125 °C		-	4.6	5.5	Α	
Reverse recovery charge Q _{rr}	0	0	T _J = 25 °C	"	-	26	=	nC
	Q _{rr}	T _J = 125 °C		-	84	-	IIC	

THERMAL - MECHANICAL SPECIFICATIONS FOR BOTH DIODES						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		- 55	-	175	°C
Thermal resistance, junction to case	R _{thJC}		-	4.1	4.8	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.2	-	C/VV
Weight			-	2.0	-	g
vveigni			-	0.07	-	OZ.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)

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Hyperfast Rectifier, 8 A Vishay High Power Products

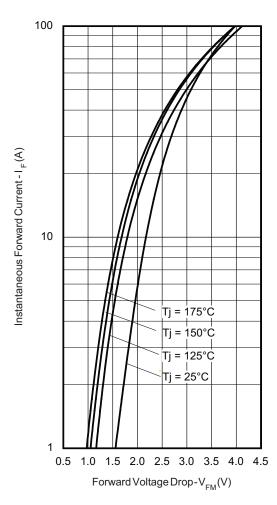


Fig. 1 - Maximum Forward Voltage Drop Characteristics

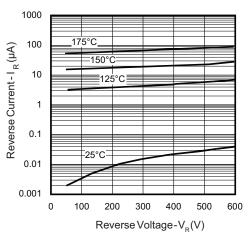


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

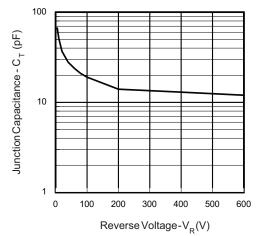


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

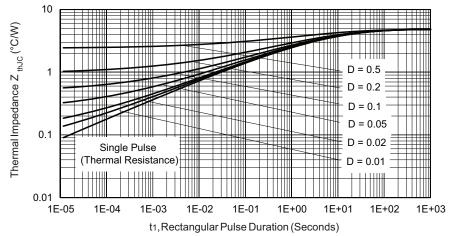


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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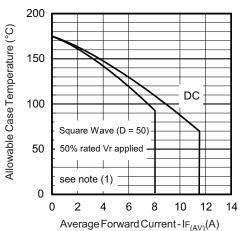


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

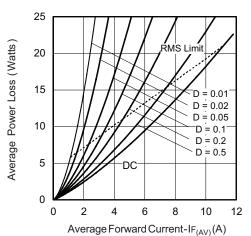


Fig. 6 - Forward Power Loss Characteristics

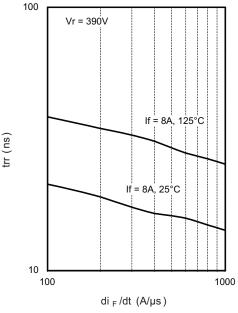


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

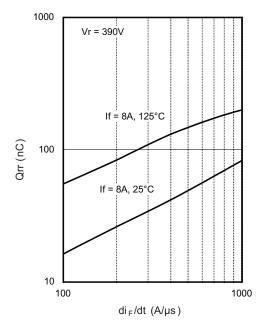


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $Pd = Forward power loss = I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); $Pd_{REV} = Inverse power loss = V_{R1} \times I_R$ (1 - D); I_R at $V_{R1} = 50$ % rated V_R

LINKS TO RELATED DOCUMENTS					
Dimensions http://www.vishay.com/doc?95263					
Part marking information	http://www.vishay.com/doc?95265				



Vishay

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